

Zlatko Sitar

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251
papers

6,213
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g-index

267
ext. papers

7,117
ext. citations

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avg, IF

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L-index

| # | Paper | IF | Citations |
|-----|--|-----|-----------|
| 251 | Ultrawide-Bandgap Semiconductors: Research Opportunities and Challenges. <i>Advanced Electronic Materials</i> , 2018 , 4, 1600501 | 6.4 | 520 |
| 250 | Growth of cubic phase gallium nitride by modified molecular-beam epitaxy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1989 , 7, 701-705 | 2.9 | 335 |
| 249 | Progress on n-type doping of AlGaIn alloys on AlN single crystal substrates for UV optoelectronic applications. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2031-2033 | | 131 |
| 248 | The 2020 UV emitter roadmap. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 503001 | 3 | 123 |
| 247 | Seeded growth of AlN bulk crystals in m- and c-orientation. <i>Journal of Crystal Growth</i> , 2009 , 312, 58-63 | 1.6 | 108 |
| 246 | On the origin of the 265 nm absorption band in AlN bulk crystals. <i>Applied Physics Letters</i> , 2012 , 100, 1919314 | 3.4 | 108 |
| 245 | Seeded growth of AlN bulk single crystals by sublimation. <i>Journal of Crystal Growth</i> , 2002 , 241, 416-420 | 1.6 | 108 |
| 244 | High internal quantum efficiency in AlGaIn multiple quantum wells grown on bulk AlN substrates. <i>Applied Physics Letters</i> , 2015 , 106, 142107 | 3.4 | 106 |
| 243 | Surface preparation and homoepitaxial deposition of AlN on (0001)-oriented AlN substrates by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2010 , 108, 043510 | 2.5 | 99 |
| 242 | Deep-Ultraviolet Light-Emitting Diodes Fabricated on AlN Substrates Prepared by Hydride Vapor Phase Epitaxy. <i>Applied Physics Express</i> , 2012 , 5, 122101 | 2.4 | 99 |
| 241 | Growth and Characterization of AlN and AlGaIn Epitaxial Films on AlN Single Crystal Substrates. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H530 | 3.9 | 98 |
| 240 | Surface kinetics in AlN growth: A universal model for the control of surface morphology in III-nitrides. <i>Journal of Crystal Growth</i> , 2016 , 438, 81-89 | 1.6 | 97 |
| 239 | Performance and Reliability of Deep-Ultraviolet Light-Emitting Diodes Fabricated on AlN Substrates Prepared by Hydride Vapor Phase Epitaxy. <i>Applied Physics Express</i> , 2013 , 6, 092103 | 2.4 | 95 |
| 238 | Lasing and longitudinal cavity modes in photo-pumped deep ultraviolet AlGaIn heterostructures. <i>Applied Physics Letters</i> , 2013 , 102, 171102 | 3.4 | 92 |
| 237 | Influence of gallium supersaturation on the properties of GaN grown by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2008 , 104, 013521 | 2.5 | 85 |
| 236 | The growth and optical properties of large, high-quality AlN single crystals. <i>Journal of Applied Physics</i> , 2004 , 96, 5870-5876 | 2.5 | 81 |
| 235 | The role of surface kinetics on composition and quality of AlGaIn. <i>Journal of Crystal Growth</i> , 2016 , 451, 65-71 | 1.6 | 80 |

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| 234 | On compensation in Si-doped AlN. <i>Applied Physics Letters</i> , 2018 , 112, 152101 | 3.4 | 71 |
| 233 | Seeded growth of AlN on N- and Al-polar AlN seeds by physical vapor transport. <i>Journal of Crystal Growth</i> , 2006 , 286, 205-208 | 1.6 | 71 |
| 232 | Doping and compensation in Al-rich AlGaN grown on single crystal AlN and sapphire by MOCVD. <i>Applied Physics Letters</i> , 2018 , 112, 062102 | 3.4 | 70 |
| 231 | Polarity Control in Group-III Nitrides beyond Pragmatism. <i>Physical Review Applied</i> , 2016 , 5, | 4.3 | 68 |
| 230 | Electron emission characteristics of GaN pyramid arrays grown via organometallic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 1998 , 84, 5238-5242 | 2.5 | 67 |
| 229 | The effect of polarity and surface states on the Fermi level at III-nitride surfaces. <i>Journal of Applied Physics</i> , 2014 , 116, 123701 | 2.5 | 64 |
| 228 | Vacancy compensation and related donor-acceptor pair recombination in bulk AlN. <i>Applied Physics Letters</i> , 2013 , 103, 161901 | 3.4 | 64 |
| 227 | Growth of Ga- and N- polar gallium nitride layers by metalorganic vapor phase epitaxy on sapphire wafers. <i>Journal of Crystal Growth</i> , 2006 , 287, 586-590 | 1.6 | 64 |
| 226 | Optically pumped UV lasers grown on bulk AlN substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 822-825 | | 62 |
| 225 | Seeded growth of AlN single crystals by physical vapor transport. <i>Journal of Crystal Growth</i> , 2006 , 287, 372-375 | 1.6 | 59 |
| 224 | Atomically Thin MoS ₂ Narrowband and Broadband Light Superabsorbers. <i>ACS Nano</i> , 2016 , 10, 7493-9 | 16.7 | 58 |
| 223 | X-Ray Photoelectron Spectroscopy Characterization of Aluminum Nitride Surface Oxides: Thermal and Hydrothermal Evolution. <i>Journal of Electronic Materials</i> , 2007 , 36, 414-419 | 1.9 | 56 |
| 222 | MgO epitaxy on GaN (0002) surfaces by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2006 , 88, 212905 | 5.4 | 56 |
| 221 | The mechanism for polarity inversion of GaN via a thin AlN layer: Direct experimental evidence. <i>Applied Physics Letters</i> , 2007 , 91, 203115 | 3.4 | 54 |
| 220 | Polarity control and growth of lateral polarity structures in AlN. <i>Applied Physics Letters</i> , 2013 , 102, 181913 | 3.4 | 52 |
| 219 | Bias voltage dependent field-emission energy distribution analysis of wide band-gap field emitters. <i>Journal of Applied Physics</i> , 1997 , 82, 5763-5772 | 2.5 | 52 |
| 218 | Comparative study of etching high crystalline quality AlN and GaN. <i>Journal of Crystal Growth</i> , 2013 , 366, 20-25 | 1.6 | 51 |
| 217 | Structural Defects in GaN Epilayers Grown by Gas Source Molecular Beam Epitaxy. <i>Materials Research Society Symposia Proceedings</i> , 1989 , 162, 537 | | 51 |

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| 216 | The role of the carbon-silicon complex in eliminating deep ultraviolet absorption in AlN. <i>Applied Physics Letters</i> , 2014 , 104, 202106 | 3.4 | 50 |
| 215 | Correlation between mobility collapse and carbon impurities in Si-doped GaN grown by low pressure metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2016 , 120, 105701 | 2.5 | 50 |
| 214 | Advances in Bulk Crystal Growth of AlN and GaN. <i>MRS Bulletin</i> , 2009 , 34, 259-265 | 3.2 | 49 |
| 213 | Design and performance of an electron cyclotron resonance plasma source for standard molecular beam epitaxy equipment. <i>Review of Scientific Instruments</i> , 1990 , 61, 2407-2411 | 1.7 | 48 |
| 212 | Stimulated emission and optical gain in AlGaIn heterostructures grown on bulk AlN substrates. <i>Journal of Applied Physics</i> , 2014 , 115, 103108 | 2.5 | 47 |
| 211 | Energy distribution of field emitted electrons from diamond coated molybdenum tips. <i>Applied Physics Letters</i> , 1997 , 70, 1596-1598 | 3.4 | 45 |
| 210 | Charge neutrality levels, barrier heights, and band offsets at polar AlGaIn. <i>Applied Physics Letters</i> , 2015 , 107, 091603 | 3.4 | 44 |
| 209 | Strain in Si doped GaN and the Fermi level effect. <i>Applied Physics Letters</i> , 2011 , 98, 202101 | 3.4 | 44 |
| 208 | Optical signature of Mg-doped GaN: Transfer processes. <i>Physical Review B</i> , 2012 , 86, | 3.3 | 43 |
| 207 | Temperature dependent photoluminescence of lateral polarity junctions of metal organic chemical vapor deposition grown GaN. <i>Journal of Applied Physics</i> , 2011 , 110, 093503 | 2.5 | 42 |
| 206 | Compensation effects in GaN:Mg probed by Raman spectroscopy and photoluminescence measurements. <i>Journal of Applied Physics</i> , 2013 , 113, 103504 | 2.5 | 40 |
| 205 | Fermi level control of compensating point defects during metalorganic chemical vapor deposition growth of Si-doped AlGaIn. <i>Applied Physics Letters</i> , 2014 , 105, 222101 | 3.4 | 40 |
| 204 | Modulated precursor flow epitaxial growth of AlN layers on native AlN substrates by metal-organic chemical vapor deposition. <i>Applied Physics Letters</i> , 2008 , 93, 022103 | 3.4 | 40 |
| 203 | Ge doped GaN with controllable high carrier concentration for plasmonic applications. <i>Applied Physics Letters</i> , 2013 , 103, 242107 | 3.4 | 38 |
| 202 | Fabrication of vertical Schottky barrier diodes on n-type freestanding AlN substrates grown by hydride vapor phase epitaxy. <i>Applied Physics Express</i> , 2015 , 8, 061003 | 2.4 | 38 |
| 201 | AlGaIn devices and growth of device structures. <i>Journal of Materials Science</i> , 2015 , 50, 3267-3307 | 4.3 | 37 |
| 200 | Point defect reduction in wide bandgap semiconductors by defect quasi Fermi level control. <i>Journal of Applied Physics</i> , 2016 , 120, 185704 | 2.5 | 37 |
| 199 | Strain relaxation by pitting in AlN thin films deposited by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2013 , 102, 061602 | 3.4 | 36 |

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| 198 | 6 kW/cm ² UVC laser threshold in optically pumped lasers achieved by controlling point defect formation. <i>Applied Physics Express</i> , 2018 , 11, 082101 | 2.4 | 35 |
| 197 | Ni/Au Schottky diodes on Al _x Ga _{1-x} N (0.7). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2407-2409 | | 35 |
| 196 | Point defect reduction in MOCVD (Al)GaN by chemical potential control and a comprehensive model of C incorporation in GaN. <i>Journal of Applied Physics</i> , 2017 , 122, 245702 | 2.5 | 34 |
| 195 | Direct determination of the silicon donor ionization energy in homoepitaxial AlN from photoluminescence two-electron transitions. <i>Applied Physics Letters</i> , 2013 , 103, 122105 | 3.4 | 33 |
| 194 | Characterization of dislocation arrays in AlN single crystals grown by PVT. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011 , 208, 1545-1547 | 1.6 | 33 |
| 193 | Simultaneous growth of a GaN p \bar{n} lateral polarity junction by polar selective doping. <i>Applied Physics Letters</i> , 2007 , 91, 212103 | 3.4 | 33 |
| 192 | Defect-free Ni/GaN Schottky barrier behavior with high temperature stability. <i>Applied Physics Letters</i> , 2017 , 110, 011603 | 3.4 | 32 |
| 191 | Different optical absorption edges in AlN bulk crystals grown in m- and c-orientations. <i>Applied Physics Letters</i> , 2008 , 93, 131922 | 3.4 | 32 |
| 190 | Two field-emission states of single-walled carbon nanotubes. <i>Applied Physics Letters</i> , 2001 , 78, 2058-2060 | 3.4 | 32 |
| 189 | Current-voltage characteristics of n \bar{n} lateral polarity junctions in GaN. <i>Applied Physics Letters</i> , 2006 , 89, 052117 | 3.4 | 30 |
| 188 | X-ray characterization of composition and relaxation of Al _x Ga _{1-x} N(0001) layers grown on GaN/sapphire templates by low pressure organometallic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2010 , 108, 043526 | 2.5 | 29 |
| 187 | Schottky contact formation on polar and non-polar AlN. <i>Journal of Applied Physics</i> , 2014 , 116, 194503 | 2.5 | 28 |
| 186 | Optical identification of silicon as a shallow donor in MOVPE grown homoepitaxial AlN. <i>Physica Status Solidi (B): Basic Research</i> , 2012 , 249, 511-515 | 1.3 | 28 |
| 185 | Fabrication of a GaN lateral polarity junction by metalorganic chemical vapor deposition. <i>Journal of Crystal Growth</i> , 2009 , 311, 3044-3048 | 1.6 | 28 |
| 184 | Study of fusion bonding of diamond to silicon for silicon-on-diamond technology. <i>Applied Physics Letters</i> , 2002 , 81, 3275-3277 | 3.4 | 28 |
| 183 | Point-Defect Nature of the Ultraviolet Absorption Band in AlN. <i>Physical Review Applied</i> , 2018 , 9, | 4.3 | 28 |
| 182 | Thermal conductivity of single-crystalline AlN. <i>Applied Physics Express</i> , 2018 , 11, 071001 | 2.4 | 27 |
| 181 | Polarity determination of polar and semipolar (112 $\bar{2}$) InN and GaN layers by valence band photoemission spectroscopy. <i>Journal of Applied Physics</i> , 2013 , 114, 173503 | 2.5 | 27 |

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| 180 | Band offsets and growth mode of molecular beam epitaxy grown MgO (111) on GaN (0002) by x-ray photoelectron spectroscopy. <i>Journal of Applied Physics</i> , 2007 , 102, 074104 | 2.5 | 27 |
| 179 | Direct Observation of Inversion Domain Boundaries of GaN on c-Sapphire at Sub-ångstrom Resolution. <i>Advanced Materials</i> , 2008 , 20, 2162-2165 | 24 | 26 |
| 178 | Growth of Bulk AlN and GaN Single Crystals by Sublimation. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 449, 41 | | 26 |
| 177 | Homoepitaxial AlN thin films deposited on m-plane (11 $\bar{0}$ 0) AlN substrates by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2014 , 116, 133517 | 2.5 | 24 |
| 176 | Characterization of Threading Dislocations in PVT-Grown AlN Substrates via x-Ray Topography and Ray Tracing Simulation. <i>Journal of Electronic Materials</i> , 2014 , 43, 838-842 | 1.9 | 24 |
| 175 | Refractive index of III-metal-polar and N-polar AlGa \bar{N} waveguides grown by metal organic chemical vapor deposition. <i>Applied Physics Letters</i> , 2013 , 102, 221106 | 3.4 | 24 |
| 174 | Sapphire decomposition and inversion domains in N-polar aluminum nitride. <i>Applied Physics Letters</i> , 2014 , 104, 032104 | 3.4 | 22 |
| 173 | Optical metastability in bulk GaN single crystals. <i>Applied Physics Letters</i> , 1997 , 71, 455-457 | 3.4 | 22 |
| 172 | The role of chemical potential in compensation control in Si:AlGa \bar{N} . <i>Journal of Applied Physics</i> , 2020 , 127, 105702 | 2.5 | 21 |
| 171 | Excitonic emission dynamics in homoepitaxial AlN films studied using polarized and spatio-time-resolved cathodoluminescence measurements. <i>Applied Physics Letters</i> , 2013 , 103, 142103 | 3.4 | 21 |
| 170 | Recovery kinetics in high temperature annealed AlN heteroepitaxial films. <i>Journal of Applied Physics</i> , 2020 , 127, 115301 | 2.5 | 20 |
| 169 | Sharp bound and free exciton lines from homoepitaxial AlN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2011 , 208, 1520-1522 | 1.6 | 20 |
| 168 | Issues and Examples Regarding Growth of AlN, GaN and Al $_x$ Ga $_{1-x}$ N Thin Films via OMVPE and Gas Source MBE. <i>Materials Research Society Symposia Proceedings</i> , 1995 , 395, 3 | | 20 |
| 167 | Thermal conductivity of GaN single crystals: Influence of impurities incorporated in different growth processes. <i>Journal of Applied Physics</i> , 2018 , 124, 105106 | 2.5 | 20 |
| 166 | Multiple Epsilon-Near-Zero Resonances in Multilayered Cadmium Oxide: Designing Metamaterial-Like Optical Properties in Monolithic Materials. <i>ACS Photonics</i> , 2019 , 6, 1139-1145 | 6.3 | 19 |
| 165 | Fermi Level Control of Point Defects During Growth of Mg-Doped GaN. <i>Journal of Electronic Materials</i> , 2013 , 42, 815-819 | 1.9 | 19 |
| 164 | High gain, large area, and solar blind avalanche photodiodes based on Al-rich AlGa \bar{N} grown on AlN substrates. <i>Applied Physics Letters</i> , 2020 , 116, 081101 | 3.4 | 18 |
| 163 | Structure of Ultrathin Native Oxides on III-Nitride Surfaces. <i>ACS Applied Materials & Interfaces</i> , 2018 , 10, 10607-10611 | 9.5 | 18 |

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| 162 | Fabrication and structural properties of AlN submicron periodic lateral polar structures and waveguides for UV-C applications. <i>Applied Physics Letters</i> , 2016 , 108, 261106 | 3.4 | 18 |
| 161 | Exciton transitions and oxygen as a donor in m-plane AlN homoepitaxial films. <i>Journal of Applied Physics</i> , 2014 , 115, 133503 | 2.5 | 17 |
| 160 | Impact of gallium supersaturation on the growth of N-polar GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2078-2080 | | 17 |
| 159 | High temperature and low pressure chemical vapor deposition of silicon nitride on AlGaIn: Band offsets and passivation studies. <i>Journal of Applied Physics</i> , 2016 , 119, 145702 | 2.5 | 17 |
| 158 | In situ mass spectrometry during diamond chemical vapor deposition using a low pressure flat flame. <i>Journal of Materials Research</i> , 1997 , 12, 2733-2742 | 2.5 | 16 |
| 157 | Surface water reactivity of polycrystalline MgO and CaO films investigated using x-ray photoelectron spectroscopy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2008 , 26, 1507-1510 | 2.9 | 16 |
| 156 | Polarity control of GaN thin films grown by metalorganic vapor phase epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2117-2120 | | 16 |
| 155 | AlN Bulk Crystal Growth by Physical Vapor Transport 2010 , 821-843 | | 16 |
| 154 | High Mg activation in implanted GaN by high temperature and ultrahigh pressure annealing. <i>Applied Physics Letters</i> , 2021 , 118, 022101 | 3.4 | 16 |
| 153 | Optical nonlinear and electro-optical coefficients in bulk aluminium nitride single crystals. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1700077 | 1.3 | 15 |
| 152 | Nonlinear analysis of vanadium- and titanium-based contacts to Al-rich n-AlGaIn. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 100302 | 1.4 | 15 |
| 151 | Implementation of the GaN lateral polarity junction in a MESFET utilizing polar doping selectivity. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010 , 207, 45-48 | 1.6 | 15 |
| 150 | Raman, photoluminescence and absorption studies on high quality AlN single crystals. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2774-2778 | | 15 |
| 149 | The polarization field in Al-rich AlGaIn multiple quantum wells. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SCCC10 | 1.4 | 14 |
| 148 | Growth of AlN crystals on AlN/SiC seeds by AlN powder sublimation in nitrogen atmosphere. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 2004 , 9, 1 | | 14 |
| 147 | Electron emission mechanism from cubic boron nitride-coated molybdenum emitters. <i>Applied Physics Letters</i> , 1998 , 72, 2909-2911 | 3.4 | 14 |
| 146 | A thermodynamic supersaturation model for the growth of aluminum gallium nitride by metalorganic chemical vapor deposition. <i>Journal of Applied Physics</i> , 2018 , 124, 115304 | 2.5 | 14 |
| 145 | Model for the deep defect-related emission bands between 1.4 and 2.4 eV in AlN. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1600714 | 1.3 | 13 |

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| 144 | Shallow Si donor in ion-implanted homoepitaxial AlN. <i>Applied Physics Letters</i> , 2020 , 116, 172103 | 3.4 | 13 |
| 143 | Dependence on pressure of the refractive indices of wurtzite ZnO, GaN, and AlN. <i>Physical Review B</i> , 2014 , 90, | 3.3 | 13 |
| 142 | High free carrier concentration in p-GaN grown on AlN substrates. <i>Applied Physics Letters</i> , 2017 , 111, 032109 | 3.4 | 13 |
| 141 | Fabrication and characterization of lateral polar GaN structures for second harmonic generation 2013 , | | 13 |
| 140 | Oxygen and silicon point defects in Al _{0.65} Ga _{0.35} N. <i>Physical Review Materials</i> , 2019 , 3, | 3.2 | 13 |
| 139 | The nature of the DX state in Ge-doped AlGa _{1-x} N. <i>Applied Physics Letters</i> , 2020 , 116, 222102 | 3.4 | 12 |
| 138 | Defect quasi Fermi level control-based CN reduction in GaN: Evidence for the role of minority carriers. <i>Applied Physics Letters</i> , 2017 , 111, 152101 | 3.4 | 12 |
| 137 | Growth and characterization of Al _x Ga _{1-x} N lateral polarity structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 1039-1042 | 1.6 | 12 |
| 136 | Free-Standing Lithium Niobate Microring Resonators for Hybrid Integrated Optics. <i>IEEE Photonics Technology Letters</i> , 2010 , 22, 251-253 | 2.2 | 12 |
| 135 | Surfactant assisted growth of MgO films on GaN. <i>Applied Physics Letters</i> , 2012 , 101, 092904 | 3.4 | 12 |
| 134 | The influence of substrate polarity on the structural quality of InN layers grown by high-pressure chemical vapor deposition. <i>Applied Physics Letters</i> , 2008 , 92, 041911 | 3.4 | 12 |
| 133 | Ammonothermal synthesis of aluminum nitride crystals on group III-nitride templates. <i>Journal of Electronic Materials</i> , 2006 , 35, 1104-1111 | 1.9 | 12 |
| 132 | Epitaxial calcium oxide films deposited on gallium nitride surfaces. <i>Journal of Vacuum Science & Technology B</i> , 2007 , 25, 1029 | | 12 |
| 131 | Hot electron transport in AlN. <i>Journal of Applied Physics</i> , 2000 , 88, 5865-5869 | 2.5 | 12 |
| 130 | Growth of AlN bulk crystals from the vapor phase. <i>Materials Research Society Symposia Proceedings</i> , 2001 , 693, 780 | | 12 |
| 129 | The effect of illumination power density on carbon defect configuration in silicon doped GaN. <i>Journal of Applied Physics</i> , 2016 , 120, 235705 | 2.5 | 12 |
| 128 | Very slow decay of a defect related emission band at 2.4 eV in AlN: Signatures of the Si related shallow DX state. <i>Journal of Applied Physics</i> , 2016 , 119, 155701 | 2.5 | 12 |
| 127 | Design of AlGa _{1-x} N-based quantum structures for low threshold UVC lasers. <i>Journal of Applied Physics</i> , 2019 , 126, 223101 | 2.5 | 12 |

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| 126 | The influence of point defects on the thermal conductivity of AlN crystals. <i>Journal of Applied Physics</i> , 2018 , 123, 185107 | 2.5 | 12 |
| 125 | Electron energy distribution of diamond-coated field emitters. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998 , 16, 716 | | 11 |
| 124 | High n-type conductivity and carrier concentration in Si-implanted homoepitaxial AlN. <i>Applied Physics Letters</i> , 2021 , 118, 112104 | 3.4 | 11 |
| 123 | UV second harmonic generation in AlN waveguides with modal phase matching. <i>Optical Materials Express</i> , 2016 , 6, 2014 | 2.6 | 11 |
| 122 | High reflectivity III-nitride UV-C distributed Bragg reflectors for vertical cavity emitting lasers. <i>Journal of Applied Physics</i> , 2016 , 120, 135703 | 2.5 | 11 |
| 121 | The role of transient surface morphology on composition control in AlGaIn layers and wells. <i>Applied Physics Letters</i> , 2019 , 114, 031602 | 3.4 | 10 |
| 120 | Optical characterization of Al- and N-polar AlN waveguides for integrated optics. <i>Applied Physics Express</i> , 2015 , 8, 042603 | 2.4 | 10 |
| 119 | Strain Recovery and Defect Characterization in Mg-Implanted Homoepitaxial GaN on High-Quality GaN Substrates. <i>Physica Status Solidi (B): Basic Research</i> , 2020 , 257, 1900705 | 1.3 | 10 |
| 118 | Control of passivation and compensation in Mg-doped GaN by defect quasi Fermi level control. <i>Journal of Applied Physics</i> , 2020 , 127, 045702 | 2.5 | 10 |
| 117 | Point defect management in GaN by Fermi-level control during growth 2014 , | | 10 |
| 116 | X-ray characterization techniques for the assessment of surface damage in crystalline wafers: A model study in AlN. <i>Journal of Applied Physics</i> , 2013 , 113, 123508 | 2.5 | 10 |
| 115 | Polarity and morphology in seeded growth of bulk AlN on SiC. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2036-2039 | | 10 |
| 114 | Frequency and Duty Cycle Dependence on the Pulsed Bias-Enhanced Nucleation of Highly Oriented Diamond on (100) Silicon. <i>Physica Status Solidi A</i> , 2001 , 186, 331-337 | | 10 |
| 113 | Status of the growth and fabrication of AlGaIn-based UV laser diodes for near and mid-UV wavelength. <i>Journal of Materials Research</i> , 2021 , 36, 4638-4664 | 2.5 | 10 |
| 112 | Complexes and compensation in degenerately donor doped GaN. <i>Applied Physics Letters</i> , 2020 , 117, 102109 | 3.0 | 10 |
| 111 | Quasi-phase-matched second harmonic generation of UV light using AlN waveguides. <i>Applied Physics Letters</i> , 2019 , 114, 103504 | 3.4 | 9 |
| 110 | On Ni/Au Alloyed Contacts to Mg-Doped GaN. <i>Journal of Electronic Materials</i> , 2018 , 47, 305-311 | 1.9 | 9 |
| 109 | Properties of AlN based lateral polarity structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 261-264 | | 9 |

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| 108 | Surface preparation of non-polar single-crystalline AlN substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 454-457 | | 9 |
| 107 | Critical examination of growth rate for magnesium oxide (MgO) thin films deposited by molecular beam epitaxy with a molecular oxygen flux. <i>Journal of Materials Research</i> , 2010 , 25, 670-679 | 2.5 | 9 |
| 106 | Spectroscopic measurements of the surface stoichiometry of chemical vapor deposited GaN. <i>Applied Physics Letters</i> , 2011 , 98, 082110 | 3.4 | 9 |
| 105 | Spectroscopic analysis of the epitaxial CaO (111)/GaN (0002) interface. <i>Applied Physics Letters</i> , 2008 , 92, 082907 | 3.4 | 9 |
| 104 | Seeded growth of AlN crystals on nonpolar seeds via physical vapor transport. <i>Journal of Electronic Materials</i> , 2006 , 35, 1513-1517 | 1.9 | 9 |
| 103 | Comparative study of textured diamond films by thermal conductivity measurements. <i>Applied Physics A: Materials Science and Processing</i> , 2006 , 85, 331-335 | 2.6 | 9 |
| 102 | Influence of relative wafer rotation on the electrical properties of the bonded SiC/SiC interface. <i>Applied Physics Letters</i> , 2004 , 84, 3993-3995 | 3.4 | 9 |
| 101 | Field emission energy distribution analysis of wide-band-gap field emitters. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1998 , 16, 689 | | 9 |
| 100 | Optical signatures of silicon and oxygen related DX centers in AlN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600749 | 1.6 | 8 |
| 99 | Smooth cubic commensurate oxides on gallium nitride. <i>Journal of Applied Physics</i> , 2014 , 115, 064101 | 2.5 | 8 |
| 98 | Slow decay of a defect-related emission band at 2.05 eV in AlN: Signatures of oxygen-related DX states. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1600338 | 1.3 | 8 |
| 97 | The effect of N-polar GaN domains as Ohmic contacts. <i>Applied Physics Letters</i> , 2010 , 97, 123502 | 3.4 | 8 |
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